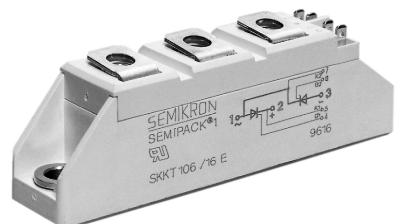


V _{RSM} V	V _{RRM} V _{DRM}	(dv/ dt) _{cr} V/μs	I _{TRMS} (maximum value for continuous operation)			
			50 A			
			I _{TAV} (sin. 180; T _{case} = 68 °C)			
			32 A			
500	400	500	—	—	SKKH 26/04 D	—
700	600	500	SKKT 26/06 D	—	SKKH 26/06 D	SKKH 27/06 D
900	800	500	SKKT 26/08 D	SKKT 27/08 D ¹⁾	SKKH 26/08 D	SKKH 27/08 D
1300	1200	1000	SKKT 26/12 E	SKKT 27/12 E ¹⁾	SKKH 26/12 E	SKKH 27/12 E
1500	1400	1000	SKKT 26/14 E	SKKT 27/14 E ¹⁾	SKKH 26/14 E	SKKH 27/14 E
1700	1600	1000	SKKT 26/16 E	SKKT 27/16 E ¹⁾	SKKH 26/16 E	SKKH 27/16 E
1900	1800	1000	SKKT 26/18 E	—	—	SKKH 27/18 E

SEMIPACK® 1 Thyristor / Diode Modules

SKKT 26 SKKH 26
SKKT 27 SKKH 27
SKKT 27B



Symbol	Conditions	SKKT 26 SKKH 26	SKKT 27 SKKT 27B	SKKH 27	Units
I _{TAV}	sin. 180; T _{case} = 68 °C T _{case} = 85 °C	32		A	
I _D	B2/B6 T _{amb} = 45 °C; P 3/180 T _{amb} = 35 °C; P 3/180 F	25 38 / 50		A	
I _{RMS}	W1/W3 T _{amb} = 45 °C; P 3/180	60 / 77 52 / 3 x 37		A	
I _{TSM}	T _{vj} = 25 °C; 10 ms T _{vj} = 125 °C; 10 ms	550		A	
i ² t	T _{vj} = 25 °C; 8,3 ... 10 ms T _{vj} = 125 °C; 8,3 ... 10 ms	480 1 500 1 150		A ² s A ² s	
t _{gd}	T _{vj} = 25 °C; I _G = 1 A dI _G /dt = 1 A/μs	1		μs	
t _{gr}	V _D = 0,67 · V _{DRM}	1		μs	
(di/dt) _{cr}	T _{vj} = 125 °C T _{vj} = 125 °C T _{vj} = 25 °C; typ./max. T _{vj} = 25 °C; R _G = 33 Ω; typ./max.	150 typ. 80 100 / 200 250 / 400		A/μs μs mA mA	
V _T	T _{vj} = 25 °C; I _T = 75 A	max. 1,8		V	
V _{T(TO)}	T _{vj} = 125 °C	0,9		V	
r _T	T _{vj} = 125 °C	12		mΩ	
I _{DD} ; I _{RD}	T _{vj} = 125 °C; V _{RD} = V _{RRM} V _{DD} = V _{DRM}	max. 10		mA	
V _{GT}	T _{vj} = 25 °C; d.c.	3		V	
I _{GT}	T _{vj} = 25 °C; d.c.	150		mA	
V _{GD}	T _{vj} = 125 °C; d.c.	0,25		V	
I _{GD}	T _{vj} = 125 °C; d.c.	5		mA	
R _{thjc}	cont. sin. 180 } per thyristor / rec. 120 } per module	0,9 / 0,45 0,95 / 0,48 1,0 / 0,5 0,2 / 0,1 – 40 ... + 125 – 40 ... + 125		°C/W °C/W °C/W °C/W °C °C	
R _{thch}					
T _{vj}					
T _{stg}					
V _{isol}	a. c. 50 Hz; r.m.s.; 1 s/1 min	3600 / 3000		V~	
M ₁	to heatsink } SI (US) units	5 (44 lb. in.) ± 15 % ²⁾		Nm	
M ₂	to terminals }	3 (26 lb. in.) ± 15 %		Nm	
a		5 · 9,81		m/s ²	
w	approx.	95		g	
Case	→ page B 1 – 95	SKKT 26: A 5 SKKH 26: A 6	SKKT 27: A 46 SKKT 27B: A 48 SKKH 27: A 47		

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.

¹⁾ Also available in SKKT 27B configuration (case A 48)
²⁾ See the assembly instructions

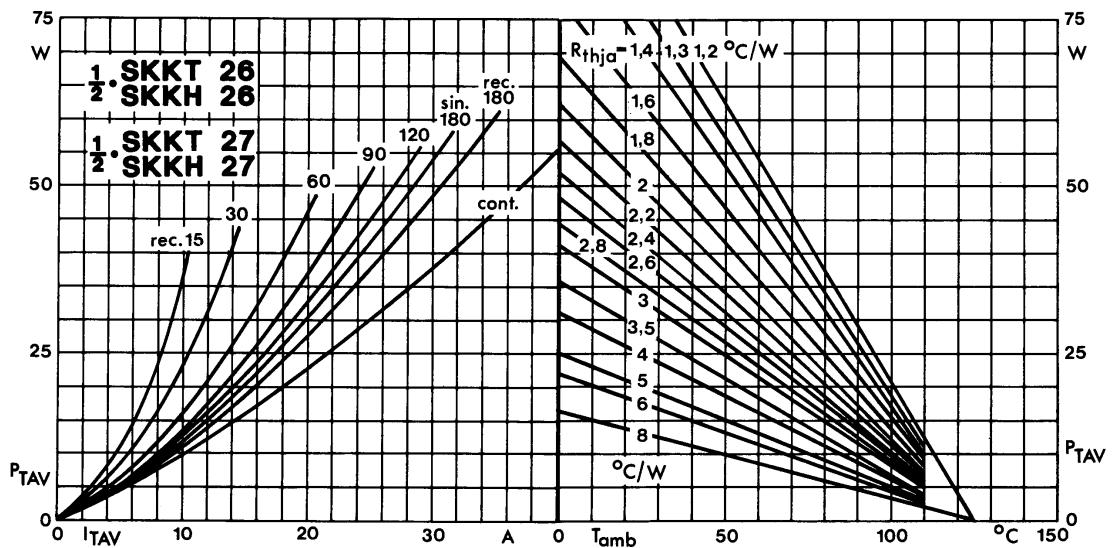


Fig. 1 Power dissipation per thyristor vs. on-state current and ambient temperature

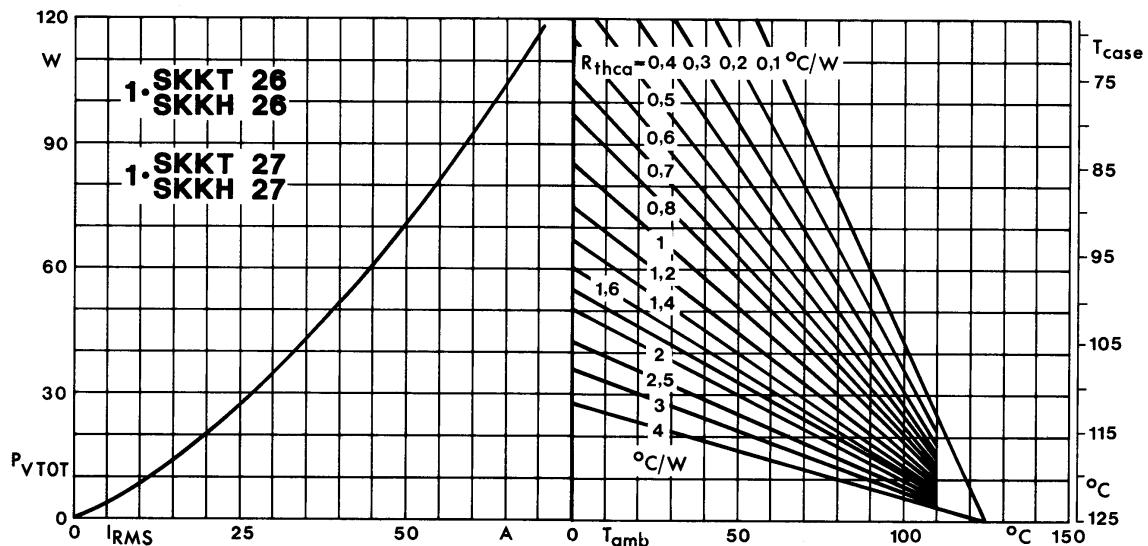


Fig. 2 Power dissipation per module vs. rms current and case temperature

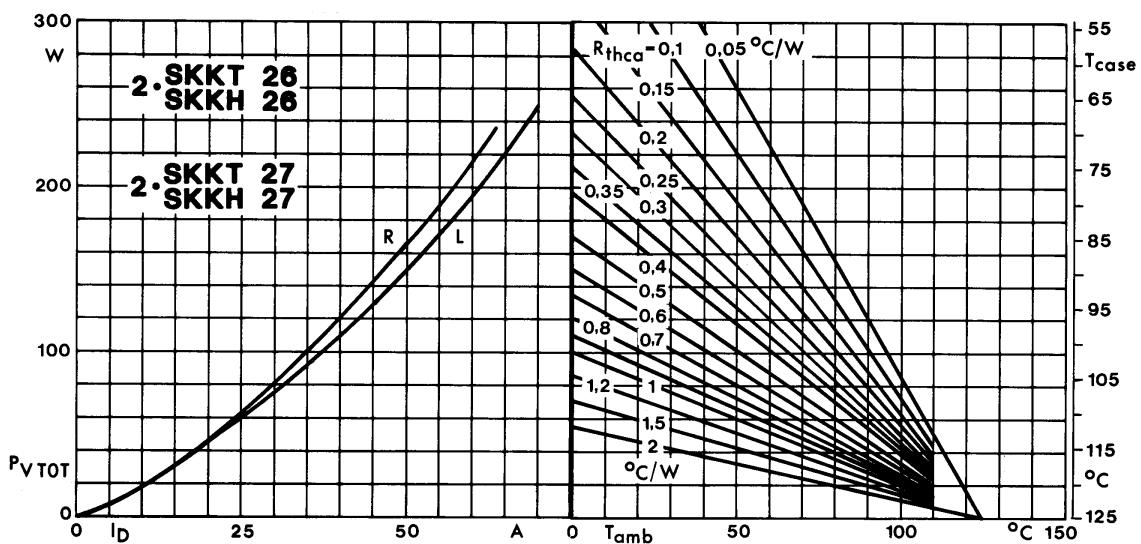


Fig. 3 Power dissipation of two modules vs. direct current and case temperature

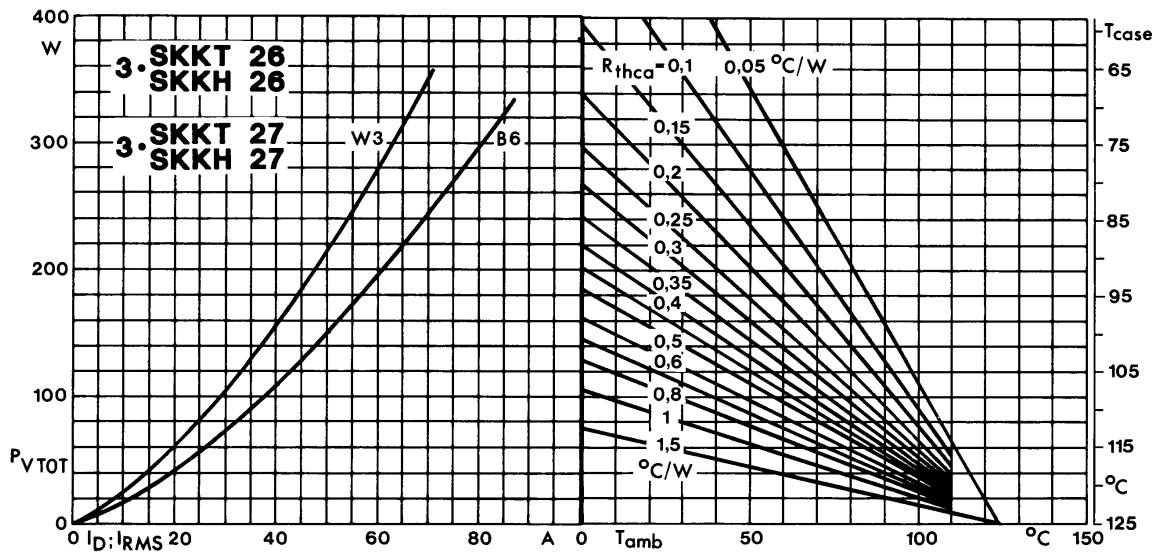


Fig. 4 Power dissipation of three modules vs. direct and rms current and case temperature

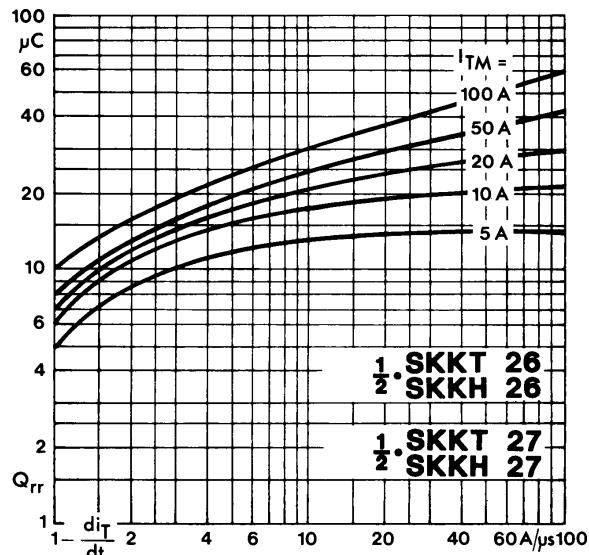


Fig. 5 Recovered charge vs. current decrease

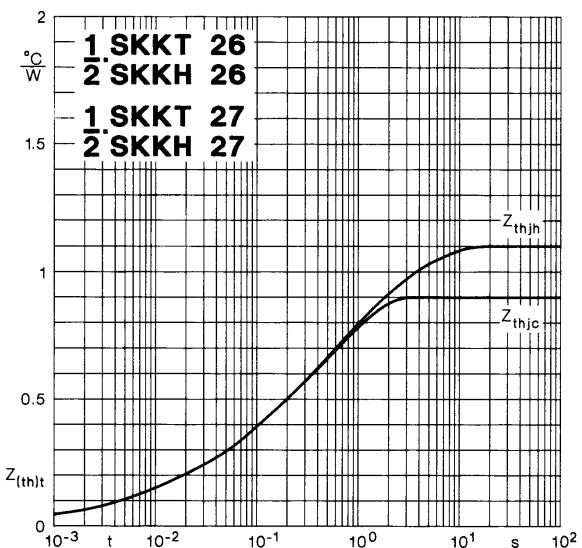


Fig. 6 Transient thermal impedance vs. time

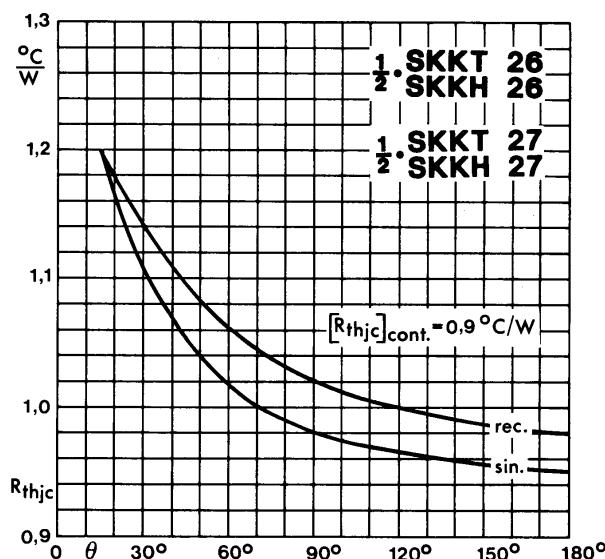


Fig. 7 Thermal resistance vs. conduction angle

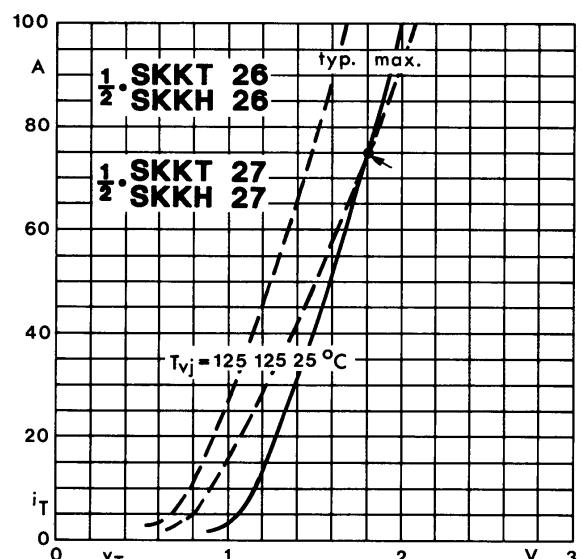


Fig. 8 On-state characteristics

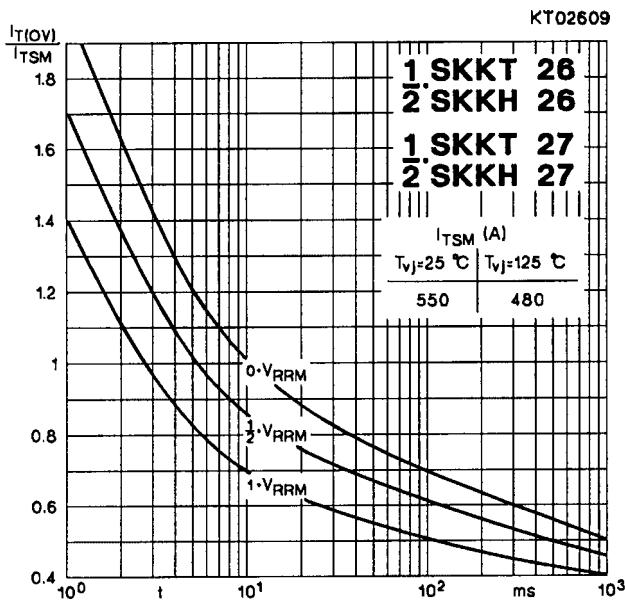


Fig. 9 Surge overload current vs. time

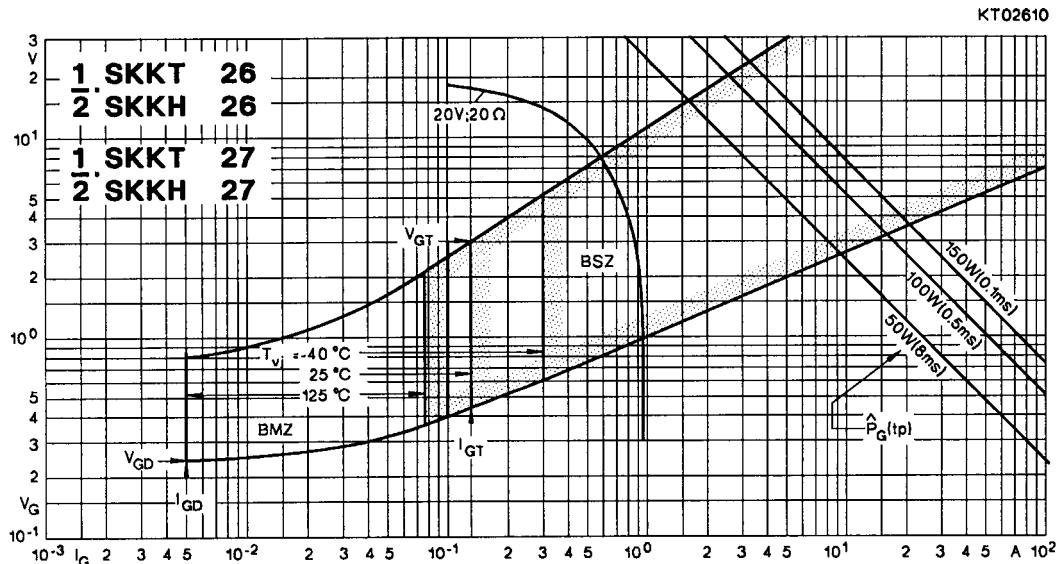


Fig. 10 Gate trigger characteristics